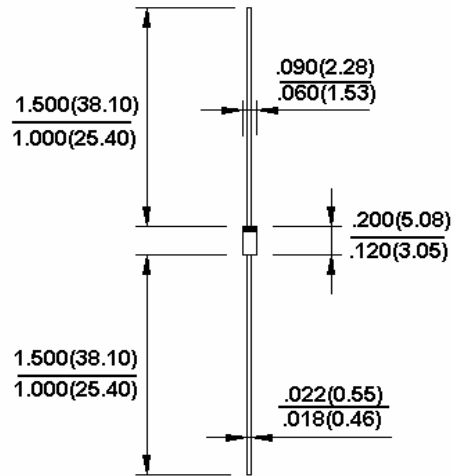


DO-35

Features

- ◇ Fast switching device ($T_{RR} < 4.0\text{nS}$)
- ◇ DO-35 package (JEDEC)
- ◇ Through-hole device type mounting
- ◇ Hermetically sealed glass
- ◇ Compression bonded construction
- ◇ All external surface are corrosion resistant and leads are readily solderable
- ◇ RoHS compliant
- ◇ Solder hot dip Tin(Sn) lead finish
- ◇ Cathode indicated by polarity band



Dimensions in inches and(millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Maximum Ratings

Type Number	Symbol	Value	Units
Power Dissipation	P_d	500	mW
Working Inverse Voltage	W_{IV}	75	V
Non-repetitive Peak Forward Current	I_{FM}	450	mA
Average Rectified Current	I_o	150	mA
Peak Forward Surge Current	I_{FSURGE}	2	A
Operating Junction Temperature	T_J	175	°C
Storage Temperature Range	T_{STG}	-65 to + 200	°C

Electrical Characteristics

Type Number	Symbol	Min	Max	Units
Breakdown Voltage $I_R=100\mu\text{A}$ $I_R=5\mu\text{A}$	B_V	100 75		V
Forward Voltage 1N4448, 1N914B $I_F=5.0\text{mA}$ 1N4148 $I_F=10\text{mA}$ 1N4448, 1N914B $I_F=100\text{mA}$	V_F	0.62	0.72 1.0 1.0	V
Reverse Leakage Current $V_R=20\text{V}$ $V_R=75\text{V}$	I_R		25 5	nA uA
Junction Capacitance $V_R=0, f=1.0\text{MHz}$	C_j	-	4.0	pF
Reverse Recovery Time (Note 1)	t_{rr}	-	4.0	nS

Notes: 1. Reverse Recovery Test Conditions: $I_F=10\text{mA}$, $V_R=6\text{V}$, $R_L=100\Omega$, $I_{RR}=1\text{mA}$



1N4448/1N4148/1N914B

500 mW Hermetically Sealed Glas Fast Switching Diodes

RATINGS AND CHARACTERISTIC CURVES (1N4448/1N4148/1N914B)

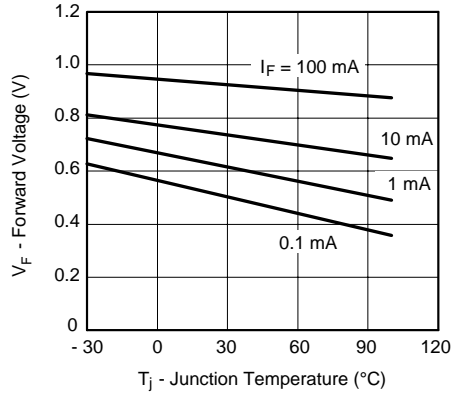


Figure 1. Forward Voltage vs. Junction Temperature

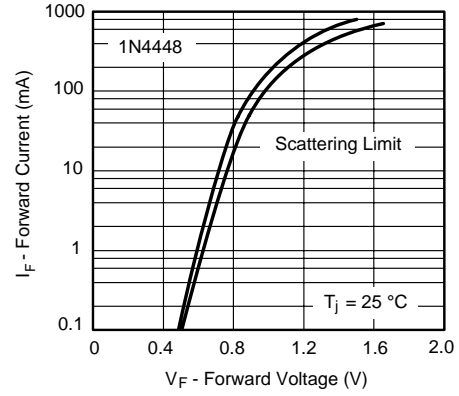


Figure 3. Forward Current vs. Forward Voltage

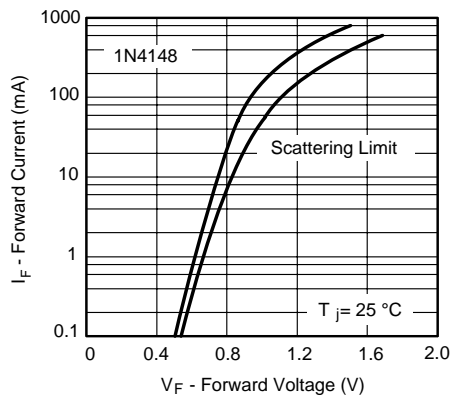


Figure 2. Forward Current vs. Forward Voltage

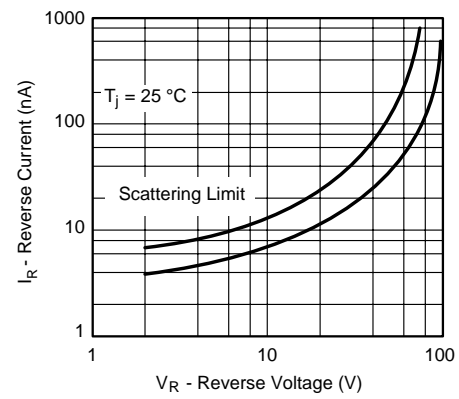


Figure 4. Reverse Current vs. Reverse Voltage